

40V, 45A,  $3.5m\Omega$  max. Silicon N Channel Power MOS FET Power Switching

### Features

- High speed switching
- Capable of 4.5 V gate drive
- Low drive current
- High density mounting

R07DS0074EJ0200

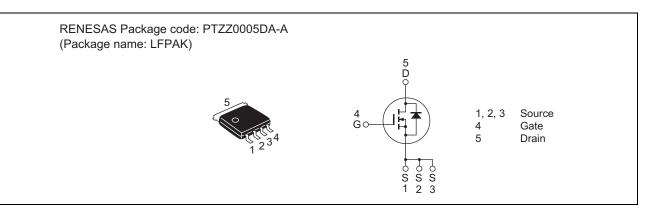
Rev.2.00

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• Low on-resistance

- $R_{DS(on)}\!=2.8~m\Omega$  typ. (at  $V_{GS}\!=10~V)$
- Pb-free
- Halogen-free

### Outline



# Application

• Switching Mode Power Supply

# **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Ratings	Unit	
Drain to source voltage	V <sub>DSS</sub>	40	V	
Gate to source voltage	V <sub>GSS</sub>	±20	V	
Drain current	I <sub>D</sub>	45	А	
Drain peak current	Note1 I <sub>D(pulse)</sub>	180	А	
Body-drain diode reverse drain current	I <sub>DR</sub>	45	А	
Avalanche current	I <sub>AP</sub> Note 2	22.5	А	
Avalanche energy	E <sub>AS</sub> Note 2	40.5	mJ	
Channel dissipation	Pch Note3	55	W	
Channel to Case Thermal Resistance	θch-C	2.27	°C/W	
Channel temperature	Tch	150	٥C	
Storage temperature	Tstg	-55 to +150	۵°	

Notes: 1.  $PW \le 10 \ \mu s$ , duty cycle  $\le 1\%$ 

2. Value at Tch = 25°C, Rg  $\geq$  50  $\Omega$ 

3. Tc = 25°C

This product is for the low voltage drive ( $\leq 10$ V).

If the driving voltage is over 10 V under normal conditions, please use the product for high gate to source cutoff voltage  $(V_{GS(off)})$  which characteristics has been improved.



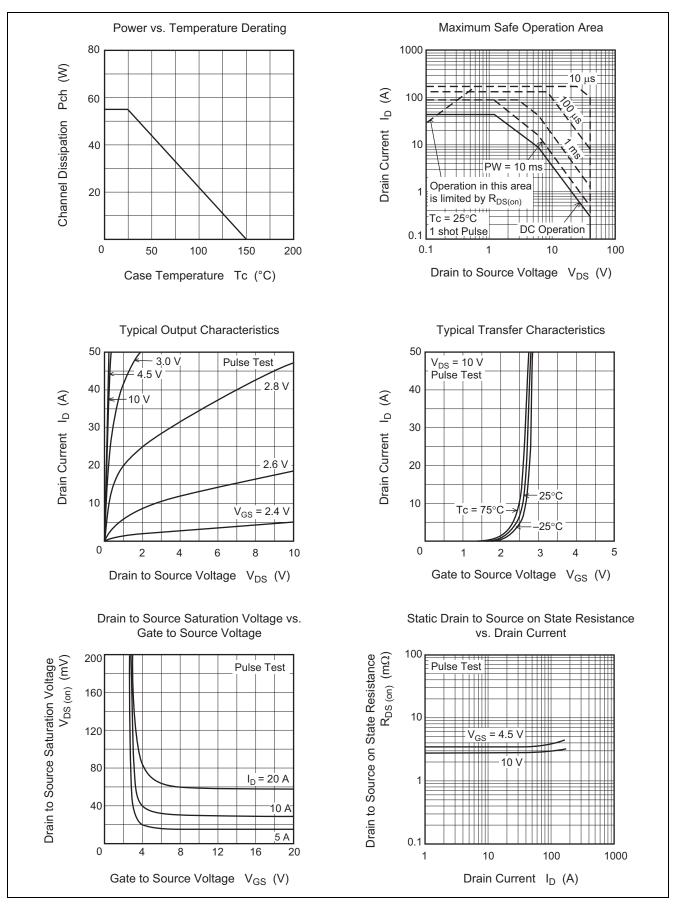
# **Electrical Characteristics**

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	40	—	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$
Gate to source leak current	I <sub>GSS</sub>	_	—	±0.1	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$
Zero gate voltage drain current	I <sub>DSS</sub>	_	—	1	μΑ	$V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}$
Gate to source cutoff voltage	V <sub>GS(off)</sub>	1.2	—	2.5	V	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$
Static drain to source on state	R <sub>DS(on)</sub>	—	2.8	3.5	mΩ	$I_D = 22.5 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$
resistance	R <sub>DS(on)</sub>	_	3.5	4.7	mΩ	$I_D = 22.5 \text{ A}, V_{GS} = 4.5 \text{ V}^{\text{Note4}}$
Forward transfer admittance	y <sub>fs</sub>	_	108		S	$I_D = 22.5 \text{ A}, V_{DS} = 10 \text{ V}^{Note4}$
Input capacitance	Ciss	_	4030	_	pF	$V_{DS} = 10 \text{ V}, \text{ V}_{GS} = 0 \text{ V},$ f = 1 MHz
Output capacitance	Coss	_	650	_	pF	
Reverse transfer capacitance	Crss	_	270	_	pF	
Gate Resistance	Rg	_	0.4	_	Ω	
Total gate charge	Qg	_	26	_	nC	$V_{DD} = 10 \text{ V}, \text{ V}_{GS} = 4.5 \text{ V},$ $I_D = 45 \text{ A}$
Gate to source charge	Qgs	_	12	_	nC	
Gate to drain charge	Qgd	_	6.6	_	nC	
Turn-on delay time	t <sub>d(on)</sub>	_	18	_	ns	
Rise time	tr	_	6.0	_	ns	
Turn-off delay time	t <sub>d(off)</sub>		65	_	ns	
Fall time	t <sub>f</sub>	_	8.5		ns	
Body-drain diode forward voltage	V <sub>DF</sub>	_	0.83	1.1	V	$I_F = 45 \text{ A}, V_{GS} = 0 \text{ V}^{Note4}$
Body–drain diode reverse recovery time	t <sub>rr</sub>		35	_	ns	I <sub>F</sub> = 45 A, V <sub>GS</sub> = 0 V di <sub>F</sub> / dt = 100 A/ μs

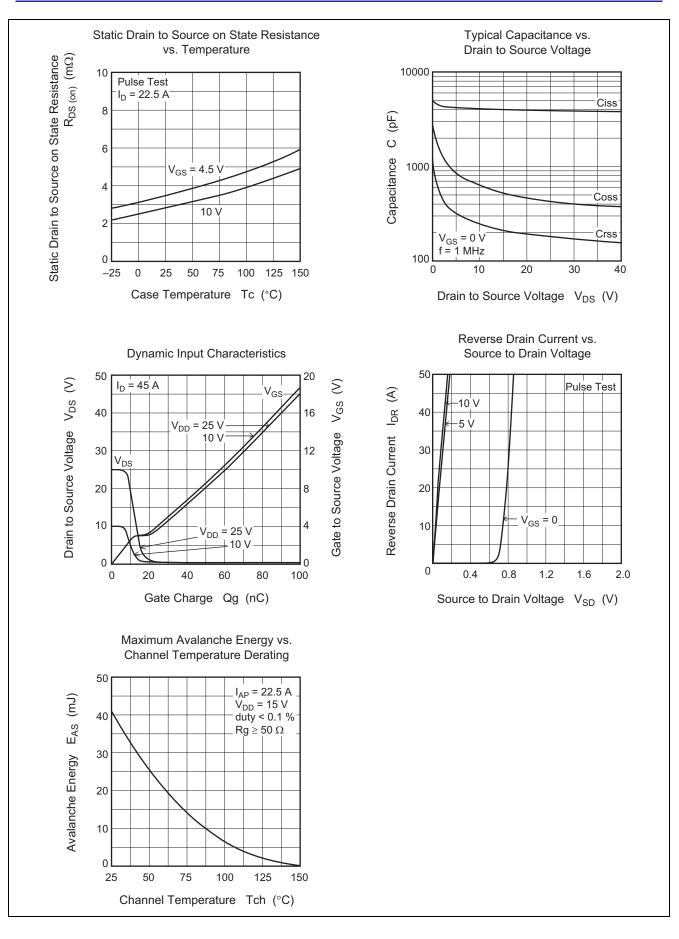
Notes: 4. Pulse test



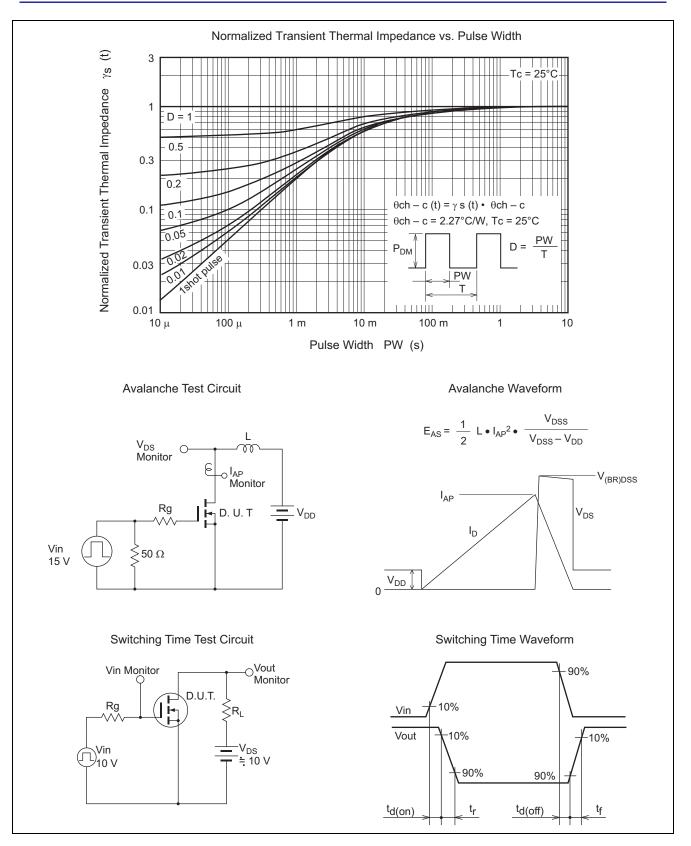
### **Main Characteristics**





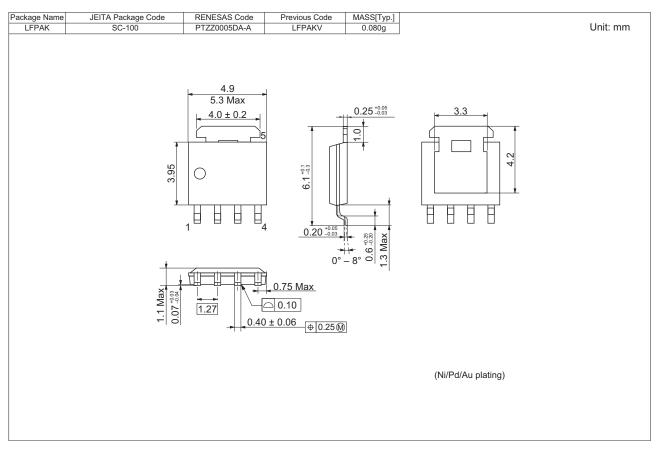








# **Package Dimensions**



## **Ordering Information**

Part No.	Quantity	Shipping Container
RJK0452DPB-00-J5	2500 pcs	Taping



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